DOCUMENT CHANGE REQUEST

DCR number 996

Changes required for: Qualification

Originator: Steve Jeffery

Date: 2016/07/22

Date sent: 2016/05/10

Organisation: ESCC Executive

Status: IMPLEMENTED

Title:	Transistor, Power MOSFET, N-Channel, Rad-Hard based on Type BUY25CS12J-01		
Number:	5205/026	Issue:	2

Other documents affected:

Page:

1, 5, 6, 7, 8, 11, 12, 13, 14, 16

Paragraph:

1.4.1, 1.4.2, 1.5, 1.6, 2.4.1, 2.4.2, 2.4.3, 2.5, 2.6, 2.10.2

Original wording:

See the existing 5205/026 Issue 2.

Proposed wording:

As per attachment 5205026 issue 3 draft B (proposed changes are highlighted).

Justification:

Infineon have requested that a new Variant (02, based on type BUY25CS04J-01) is added to this specification.

The proposed new draft (5205026 issue 3 draft B), which has been prepared by the Technical Writer, has been discussed with and agreed by Infineon.

Note that Infineon have requested that this update is made before Infineons next MOQ for their RH PowerMOS devices in September 2016.

Attachments:
5205026_issue_3_draft_b.docx
Modifications:
N/A
Approval signature:
Date signed:
2016-07-22